



mmeC

DARE180U NEW ANALOG IPs

LAURENT BERTI

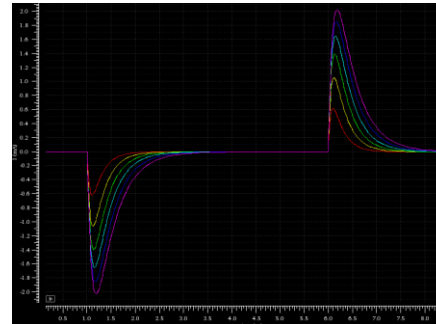
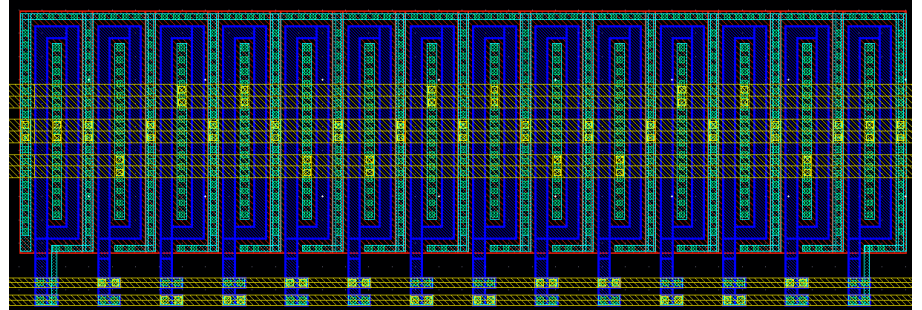
AMICSA 2018, LEUVEN

INTRODUCTION

- Technology and context
- High Density Dual Port SRAM
- General Purpose IO (GPIO) with local POC
- Voltage Monitor
- Power-On Reset
- Cristal Oscillator
- Extended Frequency Range PLL
- 11-BIT SAR ADC

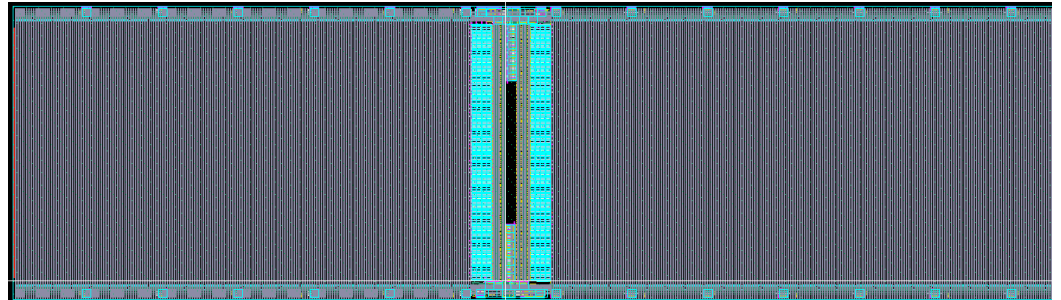
TECHNOLOGY/CONTEXT

- UMC LI80 MM/RF 1.8V/3.3V, Single Poly 6 Metal (IP6M), P-Sub/Twin-Well
- DAREI80U platform/ecosystem
 - Single Event model
 - ELT transistor
 - PCELL
 - Enhanced Model (including asymmetry...).
 - ELT aging model
 - RAD layout rule check



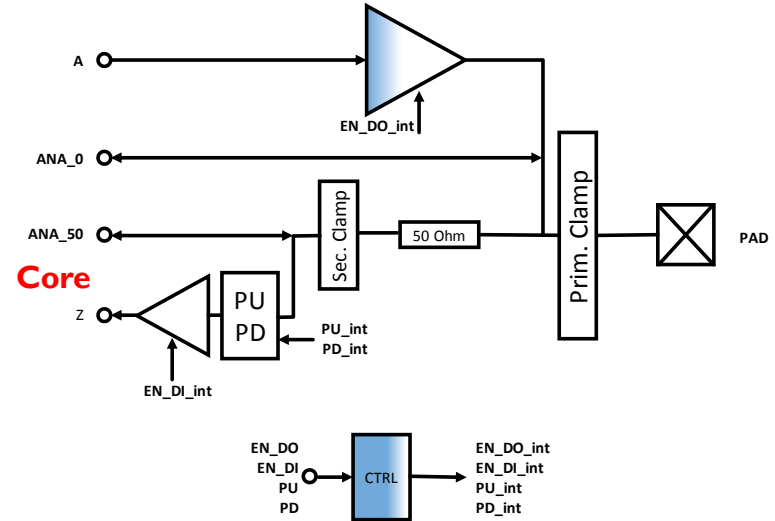
HIGH DENSITY DUAL PORT SRAM (DARE180U_HDRAM)

- High Density Dual port SRAM 4096x13 bits.
 - Clock to output available write: max. 3.8ns
 - Clock to output available read: max. 5.3ns
- Use of straight transistors only.
- Other RAD rules (N area isolation...) enforced.
- Clock tree and address decoder hardened against SET.
- Word bit's separation of 57 μ m (hardening versus MBU)
- Designed SEL free till 80 MeV*cm²/mg
- Area reduction: 50%



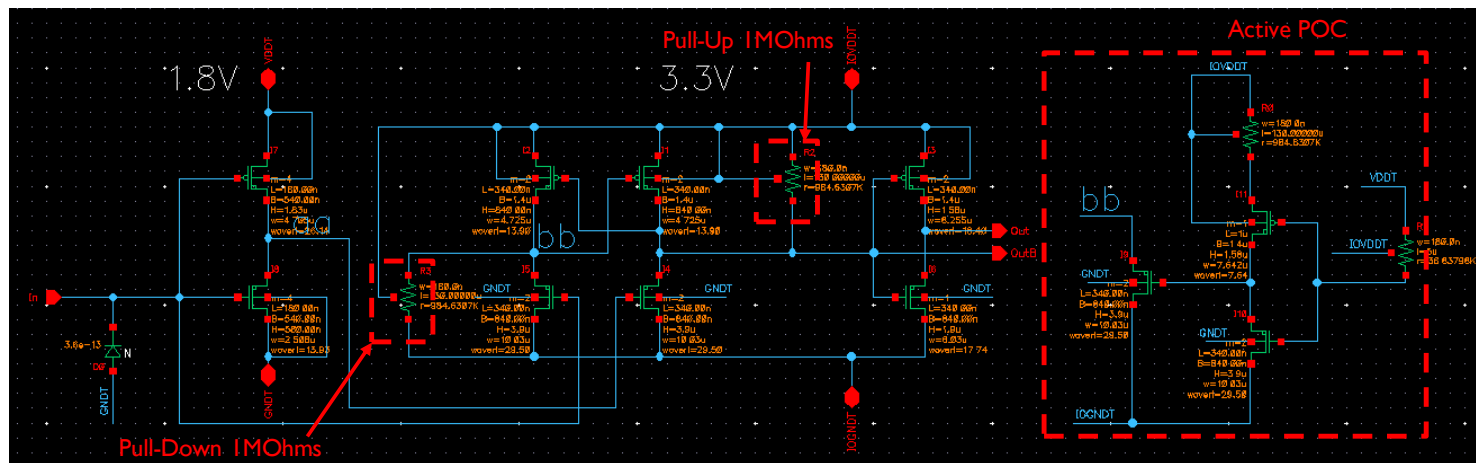
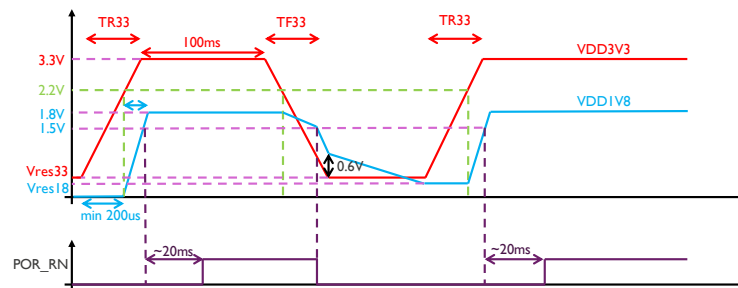
GENERAL PURPOSE IO (GPIO) WITH LOCAL POC (DAREI80U_GPIO)

- Digital input (Schmitt trigger) with programmable pull-up/pull-down
- Digital output (4mA drive)
- Analog input (serial impedance of 50 Ohms with secondary ESD protection)
- Analog output
- Designed SEL and SET free till respectively 80 and 60 MeV*cm²/mg



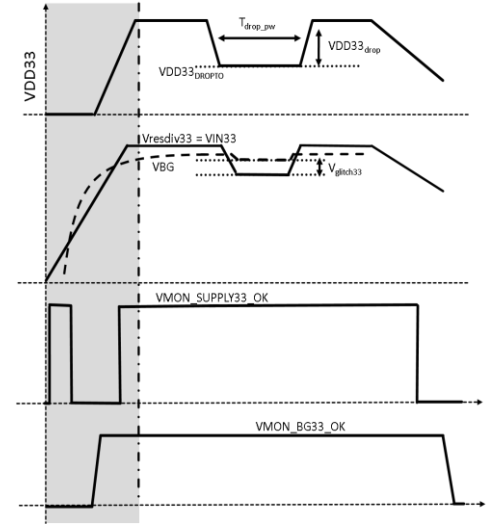
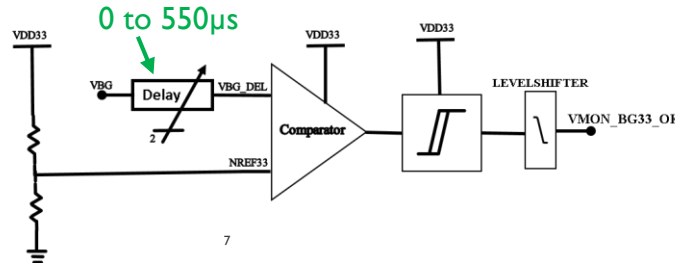
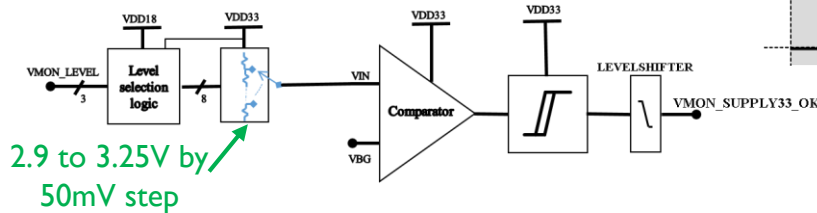
GENERAL PURPOSE IO (GPIO) WITH LOCAL POC (DAREI80U_GPIO)

- Local Power On Control (POC) to prevent glitches during the power ramp-up and the power ramp-down



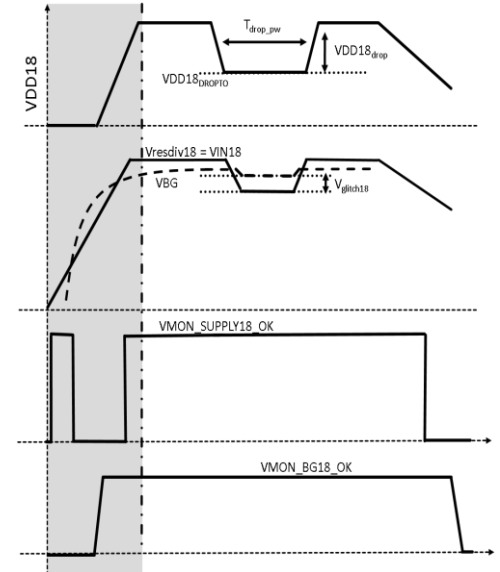
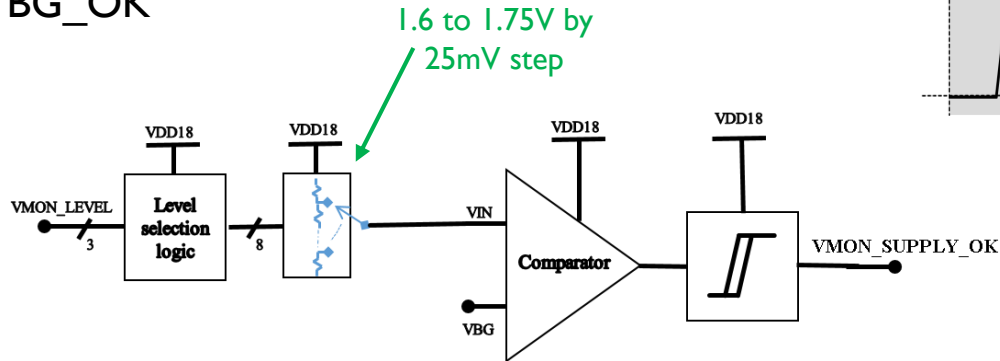
VOLTAGE MONITOR (DAREI80U_VMON)

- 3.3V voltage monitor
 - 3 bits to setup the detection level from 2.9V till 3.25V (step of 50mV)
 - Glitches filtering (20 μ s)
 - Designed SEL and SET free till respectively 80 and 60 MeV*cm²/mg
 - Hysteresis
 - Combined with BG_OK



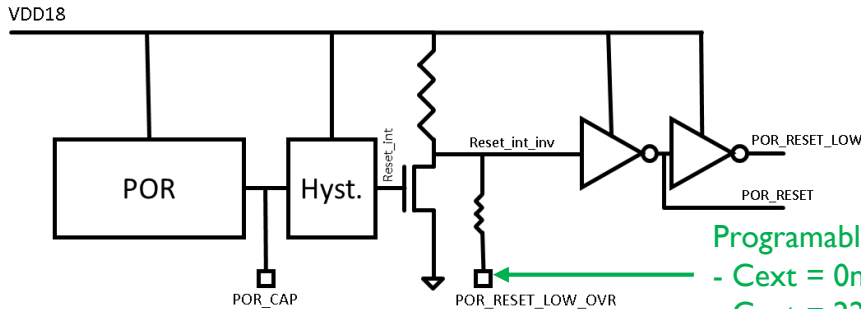
VOLTAGE MONITOR (DAREI80U_VMON)

- 1.8V voltage monitor
 - 3 bits to setup the detection level from 1.6V till 1.75V (step of 25mV)
 - Glitches filtering (20 μ s)
 - Designed SEL and SET free till respectively 80 and 60 MeV*cm²/mg
 - Hysteresis
 - Combined with BG_OK



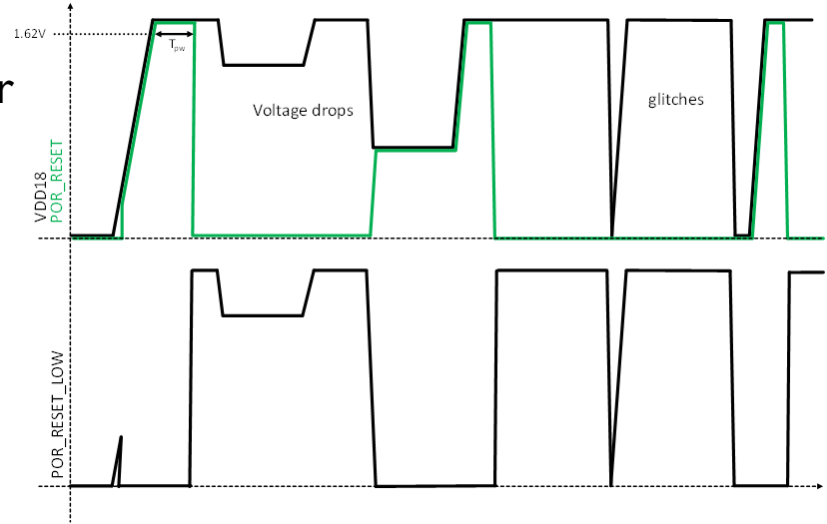
POWER-ON RESET (DAREI80U_POR)

- 1.8V detection
- Programmable reset pulse with external capacitor
- Designed SEL and SET free till respectively 80 and 60 MeV*cm²/mg



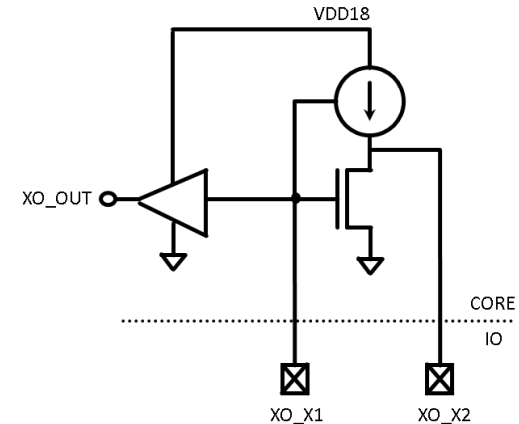
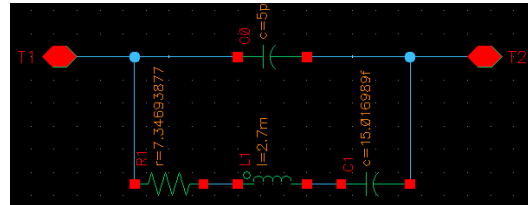
Programmable pulse width:

- Cext = 0nF => 235µs typ
- Cext = 220nF => 150ms typ



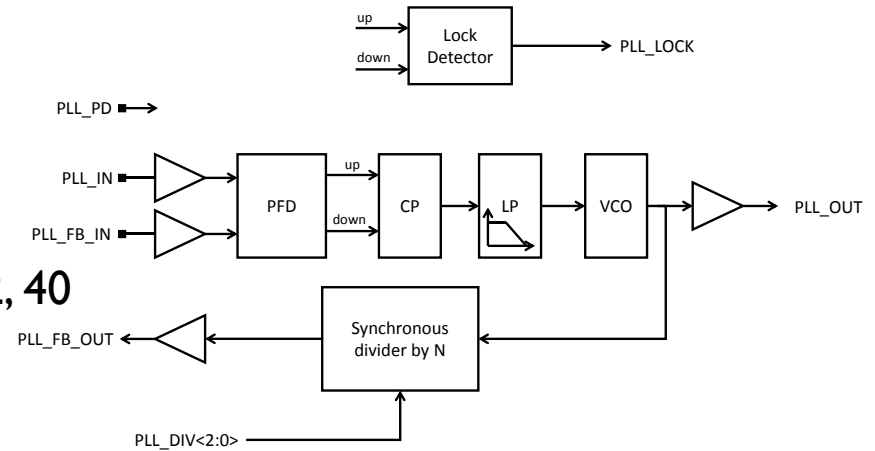
CRISTAL OSCILLATOR (DAREI80U_XO)

- Frequency range:
 - 5MHz (Rakon crystal ESCC 3501/019), 100 μ A typ., 18 ppm, startup time 1.4ms typ.
 - 25MHz (Rakon crystal ESCC 3501/01/8), 450 μ A typ., 11 ppm, startup time 1.8ms typ.
- Designed SEL free till 80 MeV*cm²/mg
- Designed SET free till 60 MeV*cm²/mg:
 - No double edge
 - Max. 1.1ns phase error at 25 MHz (~2% phase error)
 - Max. 3.8ns phase error at 5MHz (~2% phase error)



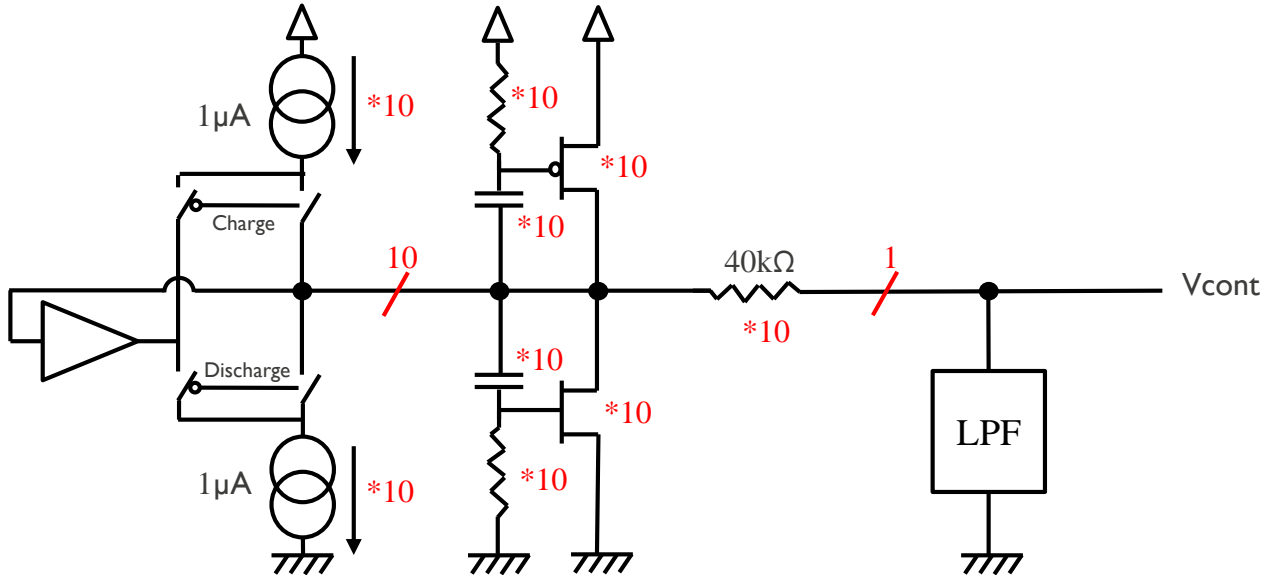
EXTENDED FREQUENCY RANGE PLL (DAREI80U_PLL_EXT)

- VCO frequency range 280MHz till 400MHz
- Designed SEL free till 80 MeV*cm²/mg
- Designed SET free till 60 MeV*cm²/mg:
 - No double edge
 - Max. 160ps phase error @F_{VCO} = 400 MHz
 - Max. 600ps phase error @F_{VCO} = 280 MHz
- Programmable frequency division: 8, 16, 20, 32, 40 and 80.
- Thermal jitter: 1ps typ



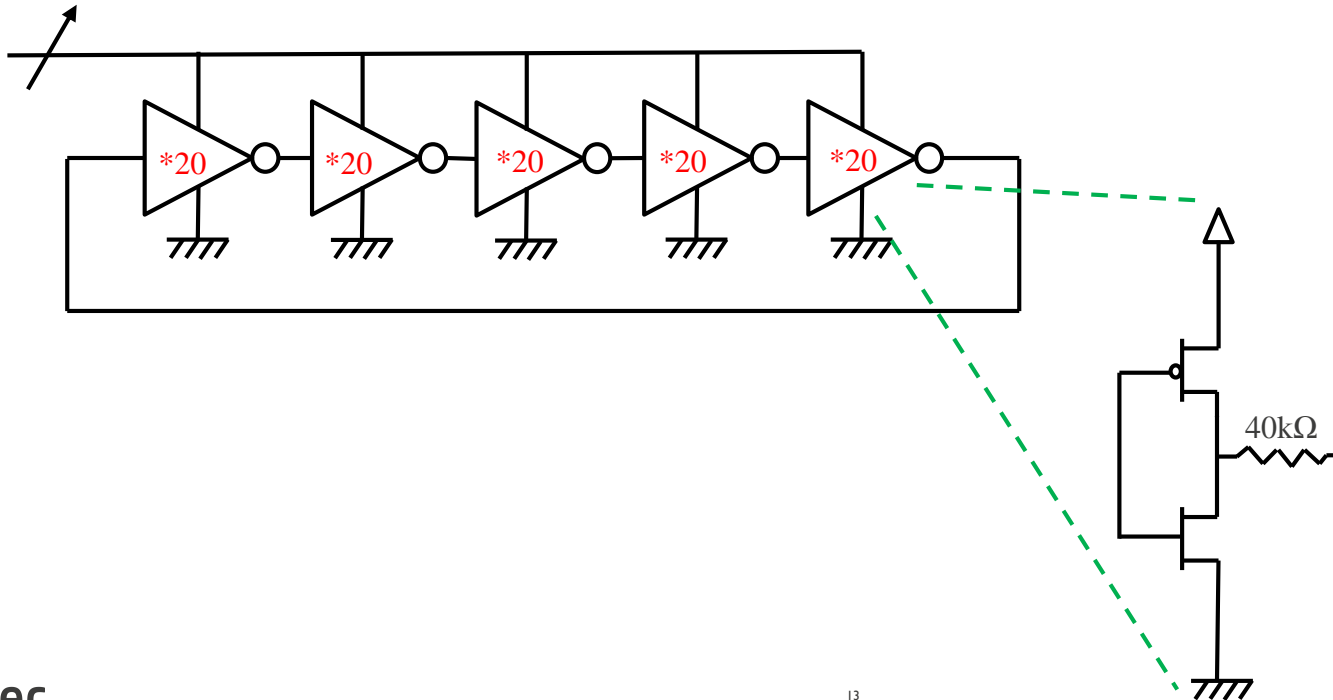
EXTENDED FREQUENCY RANGE PLL (DAREI80U_PLL_EXT) HARDENING

- PFD: by drive strength
- Synchronous divider: triplication with reset after each cycle (state-machine)
- Charge Pump: current limitation combined with clamp



EXTENDED FREQUENCY RANGE PLL (DAREI80U_PLL_EXT) HARDENING

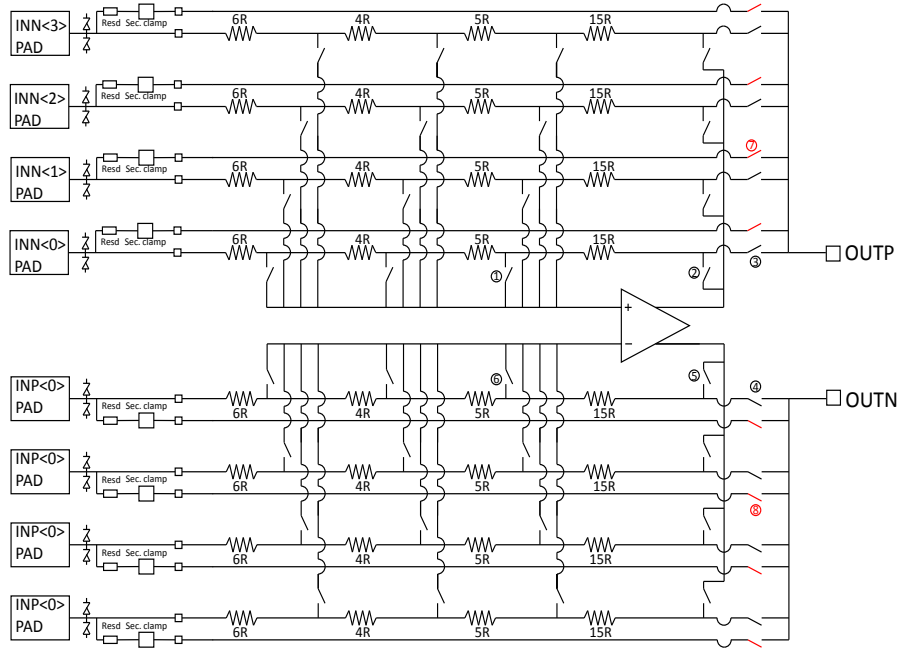
- VCO: analog averaging



11-BIT SAR ADC (DARE180U_ADC)

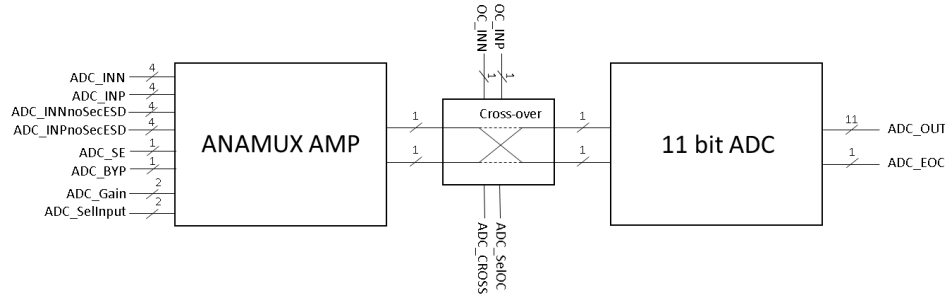
- 8:2 analog mux
 - Bypass
 - Auto zeroed differential amplifier (0dB, 6dB and 12dB).
 - Wide input common mode
 - Hardening: SET simulation result?

Gain [dB]	Min input CM [V]	Max input CM [V]	$ INP<i>- INN<i> $ [V]
0	0	VDDA	2
6	VDDA/8	7/8*VDDA	1
12	3/16*VDDA	13/16*VDDA	0.5



11-BIT SAR ADC (DARE180U_ADC)

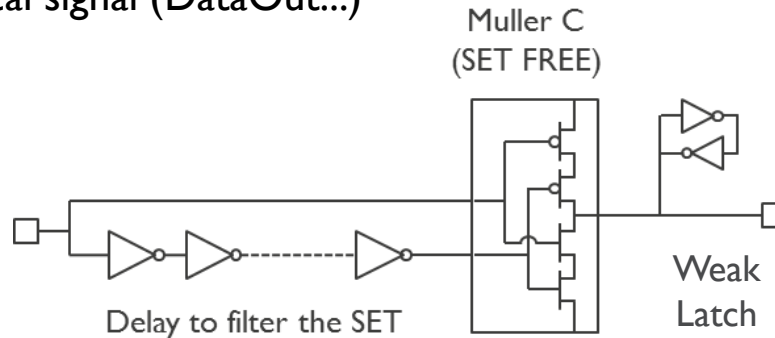
- SAR ADC configurable in differential or single-ended mode (11-bit interface, ENOB WC of 10 bits at 300kS/s)
- Internal voltage reference (external capacitor free)
- Auto zeroed comparator
- Total current consumption 5mA (including analog-mux amplifier)



11-BIT SAR ADC (DARE180U_ADC)

HARDENING

- Designed SEL free till $80 \text{ MeV} \cdot \text{cm}^2/\text{mg}$
- Digital hardening by:
 - drive strength for the critical combinatorial gates
 - Use of Hit FF
 - Signal driving switches of the capa-bank are not hardened: the SET is filtered by the limited bandwidth
 - Muller-C filter for the non critical signal (DataOut...)



11-BIT SAR ADC (DARE180U_ADC)

HARDENING

- Comparator hardening:
 - Use an auto-zeroed architecture => don't need big input transistor
 - Comparator cross section of $80\mu\text{m}^2$ @ $0.1 \text{ MeV}\cdot\text{cm}^2/\text{mg}$ for an error of 1 LSB
- Capa-bank hardening
 - Total capa-bank switches area: $240\mu\text{m}^2$
 - Cunit = 12.5 fF
 - SEU of 1 LSB correspond to $0.6 \text{ MeV}\cdot\text{cm}^2/\text{m}$



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